

Tunneling magnetoresistance of glass/Co/Al₂O₃/Fe₅₀Co₅₀/Ni₈₀Fe₂₀ nanostructures with one magnetostrictive layer

Duc N.H., Thuc V.N., Yao Y.D.

Department for Nano Magnetic Materials and Devices, College of Technology, Vietnam National University, Hanoi, 144 Xuan Thuy Road, Cau Giay, Hanoi, Viet Nam; Institute of Physics, Academia Sinica, 128 Academic Road, Taipei 115, Taiwan

Abstract: Magnetic tunnel junctions of the glass/Co(10 nm)/Al₂O₃(t_x)/Co₅₀Fe₅₀(1.8 nm)/Ni₈₀Fe₂₀(10 nm) configuration for t_x from 1.4 to 2.6 nm were fabricated by RF-sputtering. Samples were studied by means of the atomic force microscopy (AFM), high-resolution transmission electron microscopy (HR-TEM) and tunneling magnetoresistance (TMR) measurements. The tunneling magnetoresistance was investigated as a function of the thickness, as well as the oxygen concentration of the insulating layer. The optimum configuration was obtained for t_x = 1.8 nm. In this case, a magnetoresistance of 12 % was reached in an applied field of about 2 mT. From analyses of the I-V characteristics, the effective barrier width and height of the isolator turned out to be equal to 1.5 nm and 1.3 eV, respectively. These magnetic tunnel junctions can be used to design pressure sensors.

Author Keywords: AFM; HR-TEM; Strain sensor; Tunneling magnetoresistance

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Correspondence Address: Duc, N. H.; Department for Nano Magnetic Materials and Devices, College of Technology, Vietnam National University, Hanoi, 144 Xuan Thuy Road, Cau Giay, Hanoi, Viet Nam; email: ducnh@vnu.edu.vn

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Authors with affiliations:

- Duc, N.H., Department for Nano Magnetic Materials and Devices, College of Technology, Vietnam National University, Hanoi, 144 Xuan Thuy Road, Cau Giay, Hanoi, Viet Nam
- Thuc, V.N., Department for Nano Magnetic Materials and Devices, College of Technology, Vietnam National University, Hanoi, 144 Xuan Thuy Road, Cau Giay, Hanoi, Viet Nam
- Yao, Y.D., Institute of Physics, Academia Sinica, 128 Academic Road, Taipei 115, Taiwan

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